

EE466

VLSI System Design

Midterm Exam

Oct. 25, 2018. (4:15pm – 5:30pm)

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Name:

WSU ID:

Problem	Points	
1	10	
2	10	
3	5	
4	10	
5	5	
6	10	
7	10	
8	10	
Total	70	

* Allowed: Textbooks, cheat sheets, class notes, notebooks, calculators, watches

* Not allowed: Electronic devices (smart phones, tablet PCs, laptops, etc.) except calculators and watches

Problem #1 (Static CMOS Gates, 10 points).

Draw a transistor-level schematic for the following Boolean function (Available input: $A, B, C, D, \bar{A}, \bar{B}, \bar{C}, \bar{D}$). Use the static CMOS gate design. Minimize the # TRs.

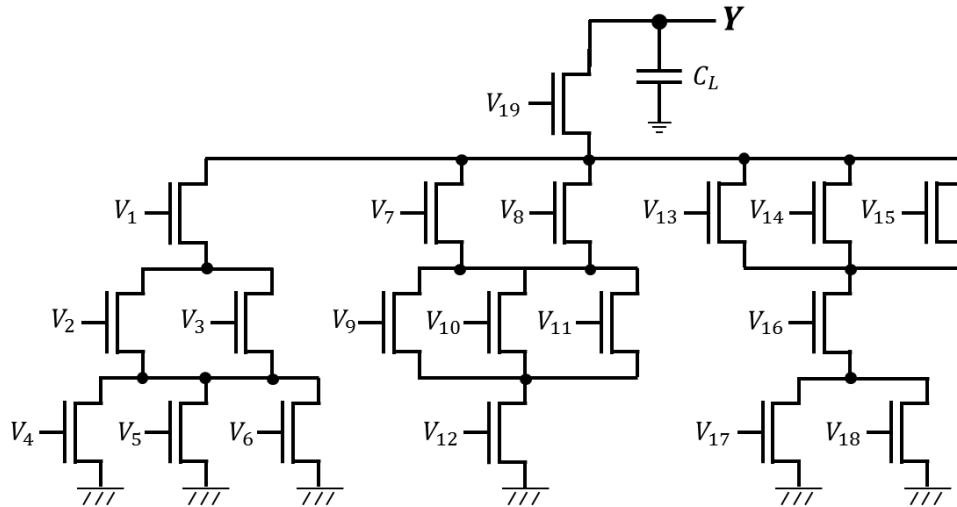
TRs ≤ 22 : 10 points. $23 \leq \# \text{ TRs} \leq 24$: 8 points. $25 \leq \# \text{ TRs} \leq 26$: 6 points. $27 \leq \# \text{ TRs}$: 4 points.

$$F = A + (B \oplus (\overline{C \oplus D}))$$

Problem #2 (Transistor Sizing, 10 points).

Size the transistors in the following pull-down network of a static CMOS gate. R_n is the resistance of a 1X NMOS transistor. C_L is the load cap. Ignore parasitic capacitances. Target timing constraint: $\tau = R_n \cdot C_L$. Try to minimize the total area.

Area $\leq 80X$: 10 points. $80X < \text{Area} \leq 82X$: 8 points. $82X < \text{Area} \leq 84X$: 6 points. $84X < \text{Area}$: 4 points.



V_1 :

V_2 :

V_3 :

V_4 :

V_5 :

V_6 :

V_7 :

V_8 :

V_9 :

V_{10} :

V_{11} :

V_{12} :

V_{13} :

V_{14} :

V_{15} :

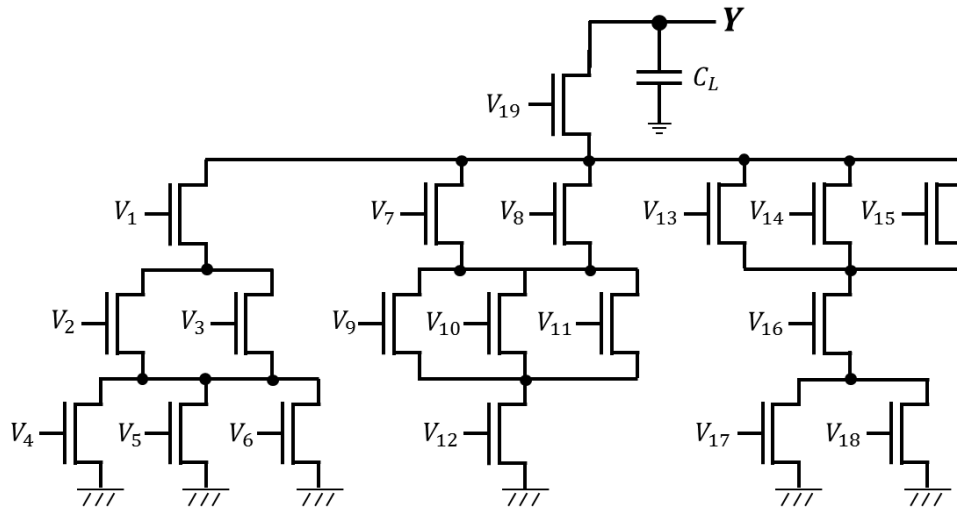
V_{16} :

V_{17} :

V_{18} :

V_{19} :

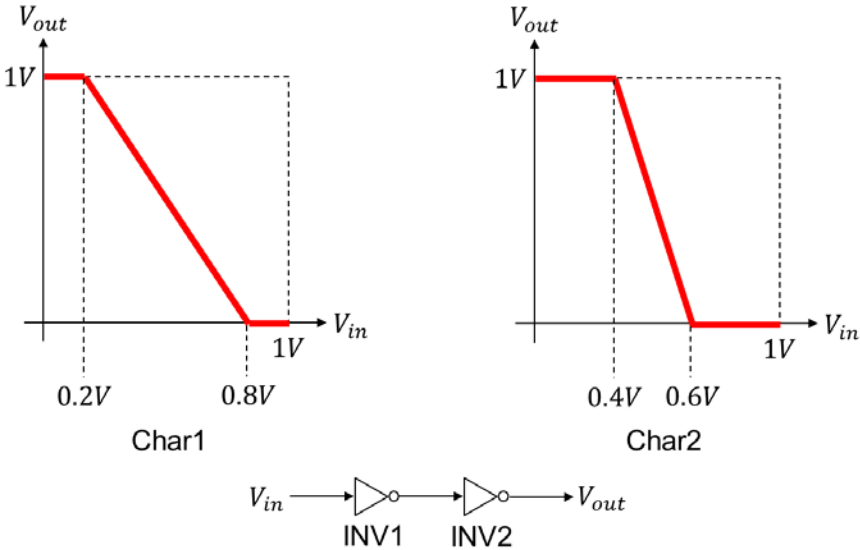
Problem #3 (Switching Analysis, 5 points).



All the transistors in the figure shown above have the same width W . Ignore parasitic RC. All the inputs are 0V at time 0. At time t , some of the input voltages switch from 0 to V_{DD} . Which one of the following has the smallest falling delay?

- 1) V_{19}, V_1, V_2, V_5 switch from 0 to VDD.
- 2) $V_{19}, V_1, V_2, V_3, V_5$ switch from 0 to VDD.
- 3) $V_{19}, V_7, V_8, V_{10}, V_{12}$ switch from 0 to VDD.
- 4) $V_{19}, V_7, V_9, V_{12}, V_{13}, V_{14}, V_{15}, V_{16}$ switch from 0 to VDD.
- 5) $V_{19}, V_1, V_2, V_6, V_7, V_9, V_{12}, V_{13}, V_{16}, V_{18}$ switch from 0 to VDD.
- 6) $V_{19}, V_1, V_2, V_4, V_7, V_8, V_9, V_{10}, V_{11}, V_{13}, V_{14}, V_{15}, V_{16}$ switch from 0 to VDD.

Problem #4 (DC Analysis, 10 points).



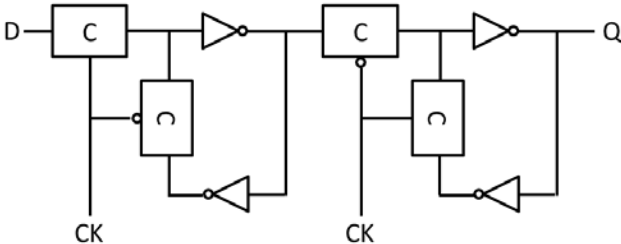
The gate-level schematic shows a buffer composed of two inverters.

1) Draw a DC characteristic curve (Char1 is for INV1 and Char2 is for INV2). You should show not only the curve, but also some important numbers in the curve.

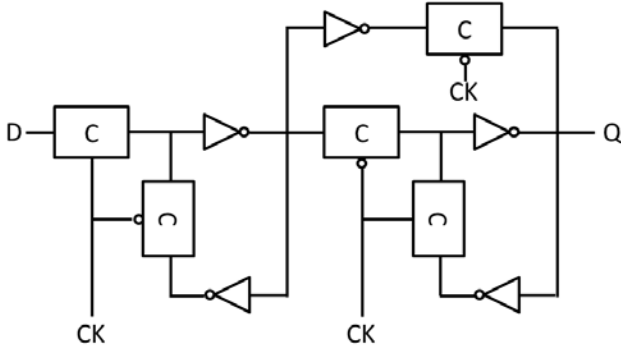
2) Draw a DC characteristic curve (Char1 is for INV2 and Char2 is for INV1). You should show not only the curve, but also some important numbers in the curve.

Problem #5 (Sequential Logic, 5 points).

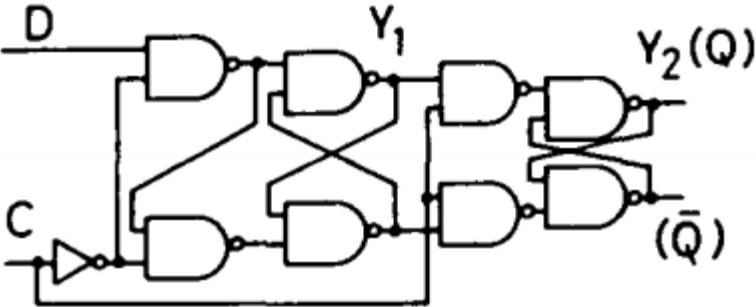
The following shows a schematic of a positive-edge-triggered D-FF.



What does the following circuit do? Can you explain any differences between the two circuits?

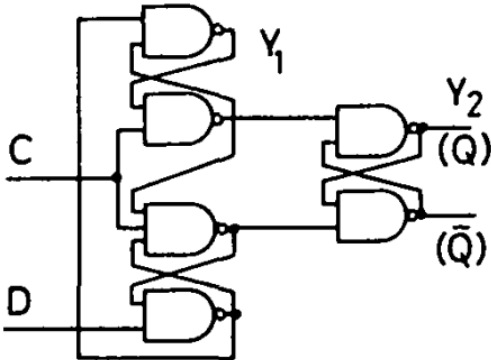


Problem #6 (Sequential Logic, 10 points).



Describe the function of the circuit shown above.

Problem #7 (Sequential Logic, 10 points).



Describe the function of the circuit shown above.

Problem #8 (Static CMOS Gates, 10 points).

Draw a dual PFET network of the following NFET network between nodes X and Y. Use eight PFETs only.

